NP50P04SDG

-40V – -50A – P-channel Power MOS FET
Application : Automotive

R07DS1520EJ0100
Rev.1.00
Jun. 17, 2022

Description

This product is P-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance : $R_{DS(on)}$ = 9.6 mΩ Max. (V_{GS} = -10 V, I_D = -25 A)
  $R_{DS(on)}$ = 15 mΩ Max. (V_{GS} = -4.5 V, I_D = -25 A)
- Low input capacitance : Ciss = 5000 pF Typ.
- Designed for automotive application and AEC-Q101 qualified.
- Pb-free (This product does not contain Pb in the external electrode)

Outline

1. Gate
2. Drain
3. Source
4. Drain(Fin)

MP-3ZK (TO-252)

Equivalent circuit

Absolute Maximum Ratings

(T_a=25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	-40	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	∓20	V
Drain Current (DC) (T_c = 25 °C)	$I_{D(DC)}$	∓50	A
Drain Current (pulse)	$I_{D(pulse)}$ Notes1	∓150	A
Total Power Dissipation (T_c = 25 °C)	P_{T1}	84	W
Total Power Dissipation (T_a = 25 °C)	P_{T2}	1.2	W
Channel Temperature	T_{ch}	175	°C
Storage Temperature	T_{stg}	-55 to 175	°C
Single Avalanche Current	I_{AS} Notes2	37	A
Single Avalanche Energy	E_{AS} Notes2	136	mJ

Notes 1. PW ≤ 10 μs , Duty Cycle ≤ 1%
2. Starting T_{ch}=25℃ , V_{DD} = -20V , R_G = 25 Ω , V_{GS} = -20 → 0V , L = 100μH

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-c)}$ Notes3	1.78	°C/W
Channel to Ambient Thermal Resistance	$R_{th(ch-a)}$ Notes3	125	°C/W

Electrical Characteristics

(T_a=25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	μA	V_{DS} = -40 V, V_{GS} = 0 V
Gate Leakage Current	I_{GSS}	—	—	∓100	nA	V_{GS} = ∓ 20 V, V_{DS} = 0 V
Gate to Source Threshold Voltage	$V_{GS(th)}$	-1.0	-1.6	-2.5	V	V_{DS} = V_{GS}, I_D = -250 μ A
Forward Transfer Admittance	| yfs | Notes4	15	33	—	S	V_{DS} = -10 V, I_D = -25 A
Drain to Source On-state Resistance	$R_{DS(on)1}$ Notes4	—	7.7	9.6	mΩ	V_{GS} = -10 V, I_D = -25 A
	$R_{DS(on)2}$ Notes4	—	9.3	15	mΩ	V_{GS} = -4.5 V, I_D = -25 A
Input Capacitance	C_{iss}	—	5000	—	pF	V_{DS} = -10 V
Output Capacitance	C_{oss}	—	770	—	pF	V_{GS} = 0 V
Reverse Transfer Capacitance	C_{rss}	—	420	—	pF	f = 1 MHz
Turn-on Delay Time	$t_{d(on)}$	—	13	—	ns	V_{DD} = -20 V
Rise Time	t_r	—	13	—	ns	I_D = -25 A
Turn-off Delay Time	$t_{d(off)}$	—	405	—	ns	V_{GS} = -10 V
Fall Time	t_f	—	180	—	ns	R_G = 0 Ω
Total Gate Charge	Q_g	—	100	—	nC	V_{DD} = -32 V
Gate to Source Charge	Q_{gs}	—	12	—	nC	V_{GS} = -10 V
Gate to Drain Charge	Q_{gd}	—	28	—	nC	I_D = -50 A
Body Diode Forward Voltage	$V_{F(S-D)}$ Notes4	—	0.95	1.5	V	I_F = -50 A, V_{GS} = 0 V
Reverse Recovery Time	t_{rr}	—	48	—	ns	I_F = -50 A, V_{GS} = 0 V
Reverse Recovery Charge	Q_{rr}	—	66	—	nC	di/dt = -100 A/μs

Notes 3. Designed target value on Renesas measurement condition. Not subject to production test.
4. Pulse test.

Typical Characteristics

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

FORWARD BIAS SAFE OPERATING AREA

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

FORWARD TRANSFER CHARACTERISTICS

GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE

FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

SWITCHING CHARACTERISTICS

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

Test Circuit

Avalanche

Test Circuit

Waveform

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \frac{V_{(BR)DSS}}{V_{(BR)DSS} - V_{DD}}$$

Switching Time

Test Circuit

Waveform

Gate Charge

Test Circuit

Waveform

Reverse Recovery

Test Circuit

Waveform

Package Dimensions

Ordering Information

Part No.	Quantity	Shipping container
NP50P04SDG-E1-AY	2500pcs/reel	Taping

Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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(Rev.5.0-1 October 2020)

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